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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown 10/789,041
	Filing Date	Even Date Herewith 2/27/04
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2818
	Examiner Name	Unknown PHAN
Sheet 1 of 8		Attorney Docket No: 1303.058US2

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
TP	US020109158	08/15/2002	Forbes, Leonard , et al.	257	224	02/09/2001
	US20020027264A1	03/07/2002	Forbes, Leonard , et al.	257	662	08/08/2001
	US20020155688	10/24/2002	Ahn, Kie Y., et al.	438	592	04/20/2001
	US20020155689	10/24/2002	Ahn, Kie Y., et al.	29	76	02/11/2002
	US20020192974	12/19/2002	Ahn, Kie Y., et al.	438	722	06/13/2001
	US20020036939A1	03/28/2002	Tsai, Wen-Jer , et al.	365	201	08/30/2001
	US20020074565A1	06/20/2002	Flagan, R. C., et al.	257	200	06/29/2001
	US20030017717	01/23/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-3,641,516	02/01/1972	Casrucci, Paul P., et al.	365	96	
	US-3,665,423	05/23/1972	Nakamura, Sho , et al.			
	US-3,877,054	04/08/1975	Boulin, David M., et al.	357	23	
	US-3,964,085	06/15/1976	Kahng, Duwon , et al.	428	428	08/18/1975
	US-4,152,627	05/01/1979	Priel, Ury , et al.	315	227	06/10/1977
	US-4,217,601	08/12/1980	DeKeersmaecker, Roger F., et al.	357	54	
	US-4,888,733	12/19/1989	Mobley, Kenneth J.	365	145	09/12/1988
	US-5,042,011	08/20/1991	Casper, Stephen L., et al.	365	205	05/22/1989
	US-5,280,205	06/18/1994	Green, Robert S., et al.	307	530	04/16/1992
	US-5,399,516	03/21/1995	Bergendahl, A. , et al.	437	43	09/21/1992
	US-5,410,504	04/25/1995	Ward, Calvin B.	365	149	05/03/1994
	US-5,457,649	10/10/1995	Eichman, Eric C., et al.	365	174	08/26/1994
	US-5,530,581	06/25/1996	Cogan, S. F.	359	265	05/31/1995
	US-5,530,668	06/25/1996	Chern, Wen-Foo , et al.	365	145	04/12/1995
	US-5,539,279	07/23/1996	Takeuchi, Kan , et al.	365	145	12/22/1994
	US-5,541,871	07/30/1996	Nishimura, K. , et al.	365	145	01/18/1995
	US-5,550,770	08/27/1996	Kuroda, Kenichi	365	145	06/02/1995
	US-5,572,459	11/05/1996	Wilson, Dennis R., et al.	365	145	09/16/1994
	US-5,600,587	02/04/1997	Koike, Hiorki	365	145	01/29/1996
✓	US-5,627,785	05/06/1997	Gilliam, Gary R., et al.	365	189.01	03/15/1996

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TP	US-5,740,104	04/14/1998	Forbes, Leonard	365	185.03	01/29/1997
	US-5,768,192	06/16/1998	Eitan, Boaz	365	185.24	07/23/1996
	US-5,801,401	09/01/1998	Forbes, Leonard	257	77	01/29/1997
	US-5,828,605	10/27/1998	Peng, K., et al.	365	185.29	10/14/1997
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
	US-5,856,688	01/05/1999	Lee, K., et al.	257	295	09/30/1997
	US-5,886,368	03/23/1999	Forbes, Leonard, et al.	257	77	07/29/1997
	US-5,912,488	06/15/1999	Kim, D. M., et al.	257	316	06/24/1997
	US-5,936,274	08/10/1999	Forbes, Leonard, et al.	257	315	07/08/1997
	US-5,943,262	08/24/1999	Choi, J.	365	185.17	10/28/1998
	US-5,973,356	10/26/1999	Noble, Wendell P., et al.	257	319	07/08/1997
	US-5,989,958	11/23/1999	Forbes, Leonard	438	257	08/20/1998
	US-5,991,225	11/23/1999	Forbes, Leonard, et al.	365	230.06	02/27/1998
	US-6,031,263	02/29/2000	Forbes, Leonard, et al.	257	315	07/29/1997
	US-6,034,882	03/07/2000	Johnson, Mark G., et al.	365	103	11/16/1998
	US-6,072,209	06/06/2000	Noble, Wendell P., et al.	257	296	07/08/1997
	US-6,115,281	09/05/2000	Aggarwal, S., et al.	365	145	09/11/1998
	US-6,125,062	09/26/2000	Ahn, Kie, et al.	365	198.07	08/26/1998
	US-6,140,181	10/31/2000	Forbes, Leonard, et al.	438	257	09/10/1999
	US-6,141,237	10/31/2000	Eliason, Jarrod, et al.	365	145	07/12/1999
	US-6,141,238	10/31/2000	Forbes, L., et al.	365	145	08/30/1999
	US-6,141,260	10/31/2000	Ahn, Kie, et al.	365	189.07	08/27/1998
	US-6,143,636	11/07/2000	Forbes, Leonard, et al.	438	587	08/20/1998
	US-6,150,687	11/21/2000	Noble, Wendell P., et al.	257	302	07/08/1997
	US-6,153,468	11/28/2000	Forbes, Leonard, et al.	438	257	05/17/1999
	US-6,166,401	12/26/2000	Forbes, L.	257	77	08/20/1998
	US-6,185,122	02/06/2001	Johnson, Mark G., et al.	365	103	12/22/1999
	US-6,203,613	03/20/2001	Gates, Stephen M., et al.	117	104	10/19/1999
✓	US-6,212,103	04/03/2001	Ahrens, Michael G., et al.	365	18529	07/28/1999

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Examiner Name	Unknown- PHAN

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TP	US-6,232,643	05/15/2001	Forbes, Leonard , et al.	257	405	11/13/1997
	US-6,238,976	05/29/2001	Noble, Wendell P., et al.	438	259	02/27/1998
	US-6,243,300	06/05/2001	Sunkavalli, Ravi S.	365	185.29	02/16/2000
	US-6,246,606	06/12/2001	Forbes, Leonard , et al.	365	185.03	09/02/1999
	US-6,249,020	06/19/2001	Forbes, Leonard , et al.	257	315	08/27/1998
	US-6,252,793	06/26/2001	Allen, Judith E., et al.	365	145	09/15/2000
	US-6,269,023	07/31/2001	Derhacobian, Narbeh , et al.	365	185.24	10/23/2000
	US-6,281,144	08/28/2001	Cleary, Thomas J., et al.	438	780	07/15/1999
	US-6,294,813	09/25/2001	Forbes, Leonard , et al.	257	321	02/15/2000
	US-6,297,539	10/02/2001	Ma, Yanjun , et al.	257	410	07/06/2000
	US-6,302,964	10/16/2001	Umotoy, Salvador P., et al.	118	715	03/16/2000
	US-6,303,481	10/16/2001	Park, Dong	438	591	12/29/2000
	US-6,313,518	11/06/2001	Ahn, K. , et al.	257	632	03/02/2000
	US-6,337,805	01/08/2002	Forbes, Leonard , et al.	365	145	12/15/1999
	US-6,351,411	02/26/2002	Forbes, Leonard , et al.	365	182	06/12/2001
	US-6,368,941	04/09/2002	Chen, Tai-Ju , et al.	438	424	11/08/2000
	US-6,380,579	04/30/2002	Nam, Sang-don , et al.	257	306	04/11/2000
	US-6,387,712	05/14/2002	Yano, Yoshihiko , et al.	438	3	12/03/1999
	US-6,391,769	05/21/2002	Lee, Jong-myeong , et al.	438	643	03/14/2000
	US-6,407,435	06/18/2002	Ma, Yanjun , et al.	257	411	02/11/2000
	US-6,432,779	08/13/2002	Hobbs, Christopher , et al.	438	287	01/30/2001
	US-6,438,031	08/20/2002	Fastow, Richard M.	365	185.18	10/26/2000
	US-6,444,039	09/03/2002	Nguyen, Tue	118	715	03/07/2000
	US-6,444,895	09/03/2002	Nikawa, Kiyoshi	136	212	09/24/1999
	US-6,445,023	09/03/2002	Vaartstra, Brian , et al.	257	295	03/16/1999
	US-6,445,030	09/03/2002	Wu, Yider , et al.	257	315	01/30/2001
	US-6,449,188	09/10/2002	Fastow, R.	365	185.18	06/19/2001
	US-6,456,531	09/24/2002	Wang, Janet S., et al.	365	185.18	06/19/2001
✓	US-6,456,536	09/24/2002	Sobek, Daniel , et al.	365	185.28	06/19/2001

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Group Art Unit	Unknown 2818
Examiner Name	Unknown PHAN

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TP	US-6,458,701	10/01/2002	Chae, Yun-sook , et al.	438	680	10/12/2000
	US-6,459,618	10/01/2002	Wang, Janet S.	365	185.18	06/13/2001
	US-6,465,334	10/15/2002	Buynoski, Matthew S., et al.	438	591	10/05/2000
	US-6,487,121	11/26/2002	Thurgate, Timothy J., et al.	365	185.18	07/05/2001
	US-6,495,436	12/17/2002	Ahn, Kie Y., et al.	438	591	02/09/2001
	US-6,498,362	12/24/2002	Forbes, Leonard , et al.	257	295	08/26/1999
	US-6,514,828	02/04/2003	Ahn, Kie Y., et al.	438	297	04/20/2001
	US-6,521,911	02/18/2003	Parsons, Gregory N., et al.	257	52	07/19/2001
	US-6,521,958	02/18/2003	Forbes, L. , et al.	257	391	08/26/1999
	US-6,534,420	03/18/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-6,545,314	04/08/2003	Forbes, Leonard , et al.			05/15/2001
	US-6,552,387	04/22/2003	Eitan, Boaz	257	324	12/14/1998
	US-6,559,014	05/06/2003	Jeon, J.	438	287	10/15/2001
	US-6,567,303	05/20/2003	Hamilton, D. G., et al.	365	185.03	01/16/2002
	US-6,567,312	05/20/2003	Torii, Satoshi , et al.	365	185.28	10/13/2000
	US-6,570,787	05/27/2003	Wang, Z. , et al.	365	185.17	04/19/2002
	US-6,580,124	06/17/2003	Cleeves, James M., et al.	257	331	08/14/2000
✓	US-6,586,785	07/01/2003	Flagan, Richard C., et al.	257	261	06/29/2001

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TP		ABBAS, S. A., et al., "N-Channel Igfet Design Limitations Due to Hot Electron Trapping", <u>Technical Digest, International Electron Devices Meeting</u> , Washington, DC, (December 1975), 35-38	
↓		ADELMANN, C , et al., "Atomic-layer epitaxy of GaN quantum wells and quantum dots on (0001) AlN", <u>Journal of Applied Physics</u> , 91(8), (April 15, 2002), 5498-5500	
↓		AHN, SEONG-DEOK , et al., "Surface Morphology Improvement of Metalorganic Chemical Vapor Deposition Al Films by Layered Deposition of Al and Ultrathin TiN", <u>Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers)</u> , 39(6A), (June 2000), 3349-3354	

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	Examiner Name	Unknown PHAN
Sheet 5 of 8	Attorney Docket No: 1303.058US2	

TP		AKASAKI, I., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N [0 < x (< or =) 0.4] Films Grown on Sapphire Substrate by MOVPE", <u>Journal of Crystal Growth</u> , 98, (1989),209-219	
		ALEN, PETRA, et al., "Atomic Layer Deposition of Ta(Al)N(C) Thin Films Using Trimethylaluminum as a Reducing Agent", <u>Journal of the Electrochemical Society</u> , 148(10), (October 2001),G566-G571	
		ASARI, K, et al., "Multi-mode and multi-level technologies for FeRAM embedded reconfigurable hardware", <u>Solid-State Circuits Conference, 1999. Digest of Technical Papers. ISSCC. 1999 IEEE International</u> , 15-17 Feb. 1999, (1999),106 -107	
		BENJAMIN, M., "UV Photoemission Study of Heteroepitaxial AlGaIn Films Grown on 6H-SiC", <u>Applied Surface Science</u> , 104/105, (September 1996),455-460	
		BERMUDEZ, V., "The Growth and Properties of Al and AlN Films on GaN(0001)-(1 x 1)", <u>Journal of Applied Physics</u> , 79(1), (January 1996),110-119	
		BRITTON, J, et al., "Metal-nitride-oxide IC memory retains data for meter reader", <u>Electronics</u> , 45(22), (October 23, 1972),119-23	
		CHAE, JUNGHUN, et al., "Atomic Layer Deposition of Nickel by the Reduction of Preformed Nickel Oxide", <u>Electrochemical & Solid-State Letters</u> , 5(6), (June 2002),C64-C66	
		CHAITSAK, SUTICAL, et al., "Cu(InGa)Se/sub 2/ thin-film solar cells with high resistivity ZnO buffer layers deposited by atomic layer deposition", <u>Japanese Journal of Applied Physics Part 1-Regular Papers Short Notes & Review Papers</u> , 38(9A), (September 1999),4989-4992	
		CRICCHI, J R., et al., "Hardened MNOS/SOS electrically reprogrammable nonvolatile memory", <u>IEEE Transactions on Nuclear Science</u> , 24(6), (December 1977),2185-9	
		DIMARIA, D J., "Graded or stepped energy band-gap-insulator MIS structures (GI-MIS or SI-MIS)", <u>Journal of Applied Physics</u> , 50(9), (September 1979),5826-5829	
		DIPERT, BRIAN, "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30(10), (October 1993),48-52	
		EITAN, BOAZ, "NR0M: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell", <u>IEEE Electron Device Letters</u> , 21(11), (November 2000),543-545	
		ELAM, J W., "Kinetics of the WF6 and Si2H6 surface reactions during tungsten atomic layer deposition", <u>Surface Science</u> , 479(1-3), (May 2001),121-135	
		FERRIS-PRABHU, A V., "Amnesia in layered insulator FET memory devices", <u>Institution of Electrical Engineers</u> , (2002),Abstract	
		FERRIS-PRABHU, A V., "Charge transfer in layered insulators", <u>Institution of Electrical Engineers</u> , (2002),Abstract	
✓		FERRIS-PRABHU, A V., "Tunnelling theories of non-volatile semiconductor memories", <u>Physica Status Solidi A</u> , 35(1), (May 16, 1976),243-50	

EXAMINER

Trong Phan

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TP		FISCH, D E., et al., "Analysis of thin film ferroelectric aging", <u>Proc. IEEE Int. Reliability Physics Symp.</u> , (1990),237-242	
		FORBES, L., et al., "Field Induced Re-Emission of Electrons Trapped in SiO", <u>IEEE Transactions on Electron Devices</u> , ED-26 (11), Briefs,(November 1979),1816-1818	
		FORSGREN, KATARINA, "Atomic Layer Deposition of HfO2 using hafnium iodide", <u>Conference held in Monterey, California</u> , (May 2001),1 page	
		FROHMAN-BENTCHKOWSKY, D, "An integrated metal-nitride-oxide-silicon (MNOS) memory", <u>Proceedings of the IEEE</u> , 57(6), (June 1969),1190-1192	
		GOODWINS, RUPERT, "New Memory Technologies on the Way", <u>http://zdnet.com.com/2100-1103-846950.html</u> , (February 2002),	
		GUHA, S, et al., "Atomic beam deposition of lanthanum-and yttrium-based oxide thin films for gate dielectrics", <u>Appl. Phys. Lett.</u> , 77, (2000),2710-2712	
		HWANG, C G., "Semiconductor Memories for the IT Era", <u>2002 IEEE International Solid-State Circuits Conference. Digest of Technical Papers IEEE</u> , Part vol. 1, San Francisco,(2002),24-27	
		HWANG, N., et al., "Tunneling and Thermal Emission of Electrons from a Distribution of Deep Traps in SiO", <u>IEEE Transactions on Electron Devices</u> , 40(6), (June 1993),1100-1103	
		JUPPO, MARIKA, et al., "Use of 1,1Dimethylhydrazine in the Atomic Layer Deposition of Transition Metal Nitride Thin Films", <u>Journal of the Electrochemical Society</u> , 147(9), (September 2000),3377-3381	
		KLAUS, J W., et al., "Atomic layer deposition of tungsten nitride films using sequential surface reactions", <u>Journal of the Electrochemical Society</u> , 147(3), (March 2000),1175-81	
		KOO, J, "Study on the characteristics of TiAlN thin film deposited by atomic layer deposition method", <u>Journal of Vacuum Science & Technology A-Vacuum Surfaces & Films</u> , 19(6), (November 2001),2831-4	
		LEI, T., "Epitaxial Growth and Characterization of Zinc-Blende Gallium Nitride on (001) Silicon", <u>Journal of Applied Physics</u> , 71(10), (May 1992),4933-4943	
		LUAN, H., "High Quality Ta2O5 Gate Dielectrics with Tox,eq<10A", <u>IEDM</u> , (1999),pp. 141-144	
		LUSKY, et al., "Characterization of channel hot electron injection by the subthreshold slope of NROM/sup TM/ device", <u>IEEE Electron Device Letters</u> , vol.22, no.11, (November 2001),556-558	
		MAAYAN, EDUARDO, et al., "A 512Mb NROM Flash Data Storage Memory with 8MB/s Data Rate", <u>Solid-State Circuits Conference, 2002. Digest of Technical Papers. ISSCC</u> , (2002),100-101	
		MARLID, BJORN, et al., "Atomic layer deposition of BN thin films", <u>Thin Solid Films</u> , 402(1-2), (January 2002),167-171	
✓		MIN, JAE-SIK, et al., "Atomic layer deposition of TiN films by alternate supply of tetrakis (ethylmethylamino)-titanium and ammonia", <u>Japanese Journal of Applied Physics Part 1-Regular Papers Short Notes & Review Papers</u> , vol.37, no.9A, (September 1998),4999-5004	

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TP		MIN, J. , "Metal-organic atomic-layer deposition of titanium-silicon-nitride films", <u>Applied Physics Letters</u> , 75(11), (1999),1521-1523	
		MOAZZAMI, R , "Endurance properties of Ferroelectric PZT thin films", <u>Int. Electron Devices Mtg., San Francisco</u> , (1990),417-20	
		MOAZZAMI, R , "Ferroelectric PZT thin films for semiconductor memory", <u>Ph.D Thesis, University of California, Berkeley</u> , (1991),	
		MOLNAR, R. , "Growth of Gallium Nitride by Electron-Cyclotron Resonance Plasma-Assisted Molecular-Beam Epitaxy: The Role of Charged Species", <u>Journal of Applied Physics</u> , 76(8), (October 1994),4587-4595	
		MORIWAKI, M , "Improved metal gate process by simultaneous gate-oxide nitridation during W/WN/sub x/gate formation", <u>Japanese Journal of Applied Physics Part 1-Regular Papers Short Notes & Review Papers</u> , 39(4B), (April 2000),2177-2180	
		NAKAJIMA, ANRI , "Soft breakdown free atomic-layer-deposited silicon-nitride/SiO/sub 2/ stack gate dielectrics", <u>International Electron Devices Meeting. Technical Digest</u> , (2001),6.5.1-4	
		PANKOVE, J. , "Photoemission from GaN", <u>Applied Physics Letters</u> , 25, (1974),53-55	
		PAPADAS, C. , "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", <u>IEEE Transaction on Electron Devices</u> , 42, (April 1995),678-682	
		PARK, JIN-SEONG , et al., "Plasma-Enhanced Atomic Layer Deposition of Tantalum Nitrides Using Hydrogen Radicals as a Reducing Agent", <u>Electrochemical & Solid-State Letters</u> , 4(4), (April 2001),C17-19	
		PUURUNEN, R L., et al., "Growth of aluminum nitride on porous silica by atomic layer chemical vapour deposition", <u>Applied Surface Science</u> , 165(2-3), (September 12, 2000),193-202	
		ROBERTSON, J. , "Band offsets of wide-band-gap oxides and implications for future electronic devices", <u>Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures)</u> , 18(3), (May-June 2000),1785-1791	
		SANDERS, B W., et al., "Zinc Oxysulfide Thin Films Grown by Atomic Layer Deposition", <u>Chemistry of Materials</u> , 4(5), (1992),1005-1011	
		SHE, MIN , et al., "Modeling and design study of nanocrystal memory devices", <u>IEEE Device Research Conference</u> , (2001),139-40	
		SHIMADA, H , et al., "Tantalum nitride metal gate FD-SOI CMOS FETs using low resistivity self-grown bcc-tantalum layer", <u>IEEE Transactions on Electron Devices</u> , vol.48, no.8, (August 200),1619-1626	
		SHIROTA, R , et al., "A 2.3 mu m/sup 2/ memory cell structure for 16 Mb NAND EEPROMs", <u>International Electron Devices Meeting 1990. Technical Digest</u> , San Francisco, (1990),103-106	
✓		SOLANKI, RAJ , et al., "Atomic Layer Deposition of Copper Seed Layers", <u>Electrochemical & Solid-State Letters</u> , 3(10), (October 2000),479-480	

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	Application Number	Unknown 10/789,041
	Filing Date	Even Date Here with 2/27/04
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2818
	Examiner Name	Unknown PHAN
Sheet 8 of 8		Attorney Docket No: 1303.058US2

TP		SZE, S M., "Physics of Semiconductor Devices", New York : Wiley, (1981),504-506	
		WEI, L S., et al., "Trapping, emission and generation in MNOS memory devices", Solid-State Electronics, 17(6), (June 1974),591-8	
		WHITE, M H., et al., "Characterization of thin-oxide MNOS memory transistors", IEEE Transactions on Electron Devices, ED-19(12), (December 1972),1280-1288	
		WHITE, M H., "Direct tunneling in metal-nitride-oxide-silicon (MNOS) structures", Programme of the 31st physical electronics conference, (1971),1	
		WILK, G. D., et al., "High-K gate dielectrics: Current status and materials properties considerations", Journal of Applied Physics, 89(10), (2001),5243-5275	
		WOOD, S W., "Ferroelectric memory design", M.A.Sc. thesis, University of Toronto, (1992),	
		YAGISHITA, A , "Dynamic threshold voltage damascene metal gate MOSFET (DT-DMG-MOS) with low threshold voltage, high drive current and uniform electrical characteristics", International Electron Devices Meeting 2000, Technical Digest, IEDM, (December 2000),663-666	
		YODER, M , "Wide Bandgap Semiconductor Materials and Devices", IEEE Transactions on Electron Devices, 43, (October 1996),1633-1636	
		ZHU, W J., et al., "Current transport in metal/hafnium oxide/silicon structure", IEEE Electron Device Letters, 23, (2002),97-99	
✓		ZHU, W , et al., "HfO2 and HfAlO for CMOS: Thermal Stability and Current Tranport", IEEE International Electron Device Meeting 2001, (2001),463-466	

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